Optoschmitt Detector 10 k Ohm Pull-Up Output

FEATURES

- Side-looking plastic package
- 55° (nominal) acceptance angle
- TTL/LSTTL/CMOS compatible
- 10Ω pull- up output
- Buffer or inverting logic available
- High noise immunity output
- Mechanically and spectrally matched to SEP8506 and SEP8706 infrared emitting diodes



The SDP8604/8614 series consists of a high speed IC molded in a side-looking black plastic package to minimize the effect of visible ambient light. The detector incorporates a Schmitt trigger which provides pulse shaping and hysteresis for noise immunity. Detector output is an NPN silicon transistor with a 10 $k\Omega$ (nominal) pull-up resistor. This option eliminates the need for an external load resistor to generate an output signal voltage. Output rise and fall times are independent of rate of change of incident light. Detector sensitivity has been internally temperature compensated. For additional output configuration options refer to SDP8004/8014 and SDP8304/8314.

Device Polarity:

Buffer - Output is HI when incident light intensity is above the turn- on threshold level.

Inverter - Output is LO when incident light intensity is above the turn- on threshold level.



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OUTLINE DIMENSIONS in inches (mm)

Tolerance

3 plc decimals ±0.005(0.12) 2 plc decimals ±0.020(0.51)



DIM 026 ds4

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192

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ELECTRICAL CHARACTERISTICS (-40°C to +85°C unless otherwise noted)						
PARAMETER	SYMBOL	MIN	TYP	MAX	UNITS	TEST CONDITIONS
Operating Supply Voltage	Vcc	4.5		12.0	V	T _A =25°C
Turn-on Threshold Irradiance (2) SDP8604-301, SDP8614-301	Eet(+)	0.06		0.37	mW/cm ²	Vcc=5 V T _A =25°C
Hysteresis (3)	HYST	33		67	%	
Supply Current	lcc			15.0	mA	V _{cc} =12 V E _e =0 Or 3.0 mW/cm ²
High Level Output Voltage SDP8604 SDP8614	Vон	2.4 2.4			V	Vcc=4.5 V, Іон=0 Ee=3.0 mW/cm² Ee=0
Low Level Output Voltage SDP8604 SDP8614	Vol			0.4 0.4	V	V _{cc} =4.5 V, I _{oL} =12.8 mA Ee=0 Ee=3.0 mW/cm²
Internal Pull-Up Resistor	RINT	5.0	10.0	20.0	kΩ	
Operate Point Temperature Coefficient			-0.76		%/°C	Emitter @ Constant Temperature
Output Rise Time, Output Fall Time	tr, tf		70		ns	Vcc=5 V, T _A =25°C Ee=0 or 3.0 mW/cm ² f=10.0 kHz, D.C.=50% R _L =390 Ω
Propagation Delay, Low-High, High-Low	tрլн, tрнг		2.5	5.0	μs	V _{CC} =5 V, T _A =25°C Ee=0 or 3.0 mW/cm ² f=10.0 kHz, D.C.=50% R _L =390 Ω
Clock Frequency				100	kHz	R∟=390 Ω, C∟=50 pF

Notes

It is recommended that a bypass capacitor, 0.1 µF typical, be added between V_{CC} and GND near the device in order to stabilize power supply line.
The radiation source is an IRED with a peak wavelength of 935 nm.
Hysteresis is defined as the difference between the operating and release threshold intensities, expressed as a percentage of the operate threshold intensity.

12 V (1)

ABSOLUTE MAXIMUM RATINGS

(25°C Free-Air Temperature unless otherwise noted)

Supply Voltage Duration of Output Short to Vcc or Ground

Low Level Output Current Irradiance Operating Temperature Range Storage Temperature Range Soldering Temperature (5 sec)

Notes

1. Derate linearly from 25°C to 5.5 V at 85°C.



1.0 sec 16.0 mA 25 mW/cm² -40°C to 85°C -40°C to 85°C 240°C



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SWITCHING WAVEFORM FOR BUFFERS









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194

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All Performance Curves Show Typical Values

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60 80 100